

3-phase bridge inverter

SKiiP 26AC12T4V1

Features

- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

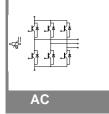
- Inverter up to 29 kVA
- Typical motor power 18,5 kW

Remarks

- V_{CEsat}, V_F= chip level value
 Case temp. limited to T_C = 125°C max. (for baseplateless modules $T_{\rm C} = T_{\rm S}$)
- product rel. results valid for $T_{i} \le 150$ (recomm. $T_{op} = -40$... +150°C)

Absolute Maximum Ratings			$T_c = 25 \text{ °C}$, unless otherwise spe			
Symbol	Conditions		Values	Units		
IGBT						
V _{CES}	T _j = 25 °C		1200	V		
Ι _C	T _j = 175 °C	T _c = 25 °C	90	А		
		T _c = 70 °C	73	А		
I _{CRM}	I _{CRM} = 3xI _{Cnom}		210	А		
V_{GES}			±20	V		
t _{psc}	V_{CC} = 800 V; $V_{GE} \le 15$ V; VCES < 1200 V	T _j = 150 °C	10	μs		
Inverse	Diode					
I _F	T _j = 175 °C	T _c = 25 °C	82	А		
		T _c = 70 °C	66	А		
I _{FRM}	I _{CRM} = 3xI _{Cnom}		225	А		
I _{FSM}	t _p = 10 ms; sin.	T _j = 150 °C	429	А		
Module						
I _{t(RMS)}			100	А		
T _{vj}			-40+175	°C		
T _{stg}			-40+125	°C		
V _{isol}	AC, 1 min.		2500	V		

Characteristics T _c =		25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT						_
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = 2 \text{ mA}$		5	5,8	6,5	V
I _{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T _j = 25 °C			0,3	mA
V _{CE0}		T _j = 25 °C		0,8	0,9	V
		T _j = 150 °C		0,7	0,8	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		15	16,5	mΩ
		T _j = 150°C		22	23,5	mΩ
V _{CE(sat)}	I _{Cnom} = 70 A, V _{GE} = 15 V			1,85	2,05	V
		T _j = 150°C _{chiplev.}		2,25	2,45	V
C _{ies}				3,9		nF
C _{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		0,31		nF
C _{res}				0,23		nF
Q_{G}	V _{GE} = -8V +15V			400		nC
R _{Gint}	T _j = 25 °C			0		Ω
t _{d(on)}				26		ns
t,	$R_{Gon} = 9,1 \Omega$	V _{CC} = 600V		36		ns
E _{on}	di/dt = 1820 A/µs	I _C = 75A		9,5		mJ
t _{d(off)}	$R_{Goff} = 9,1 \Omega$	$T_{j} = 150 \ ^{\circ}C$		320		ns
t _f	di/dt = 900 A/µs	$V_{GE} = \pm 15V$		175		ns
E _{off}				7,1		mJ
R _{th(j-s)}	per IGBT			0,55		K/W





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Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse D							
$V_F = V_{EC}$	I_{Fnom} = 75 A; V_{GE} = V			2,2	2,5	V	
		T _j = 150 °C _{chiplev.}		2,1	2,45	V	
V _{F0}		T _j = 25 °C		1,3	1,5	V	
		T _j = 150 °C		0,9	1,1	V	
r _F		T _j = 25 °C		12	13	mΩ	
		T _j = 150 °C		16	18	mΩ	
I _{RRM}	I _F = 75 A	T _i = 150 °C		80		А	
Q _{rr}	di/dt = 2120 A/µs			13,3		μC	
E _{rr}	$V_{GE} = \pm 15V$			5,6		mJ	
R _{th(j-s)}	per diode			0,75		K/W	
M _s	to heat sink					Nm	
M _t	to terminals		2		2,5	Nm	
w				65		g	
Temperat	ture sensor						
R _{ts}	3%, Tr = 25°C			1000		Ω	
R _{ts}	3%, Tr = 100°C			1670		Ω	

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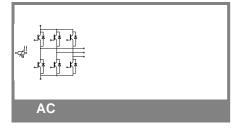
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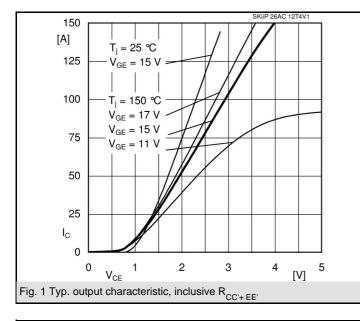
Remarks

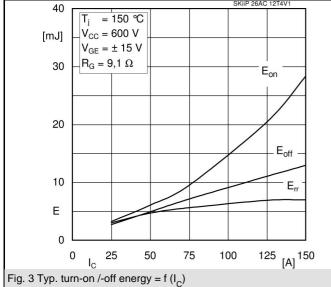
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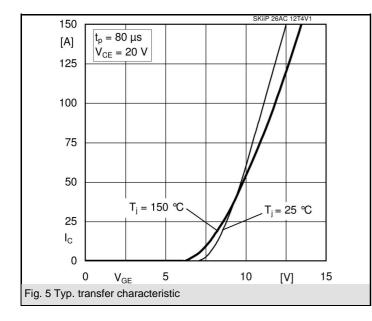
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

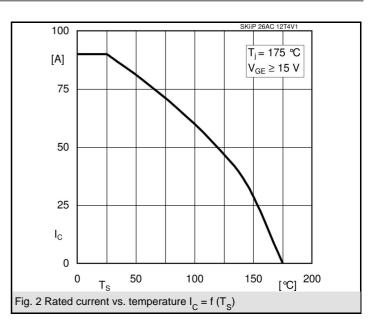
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

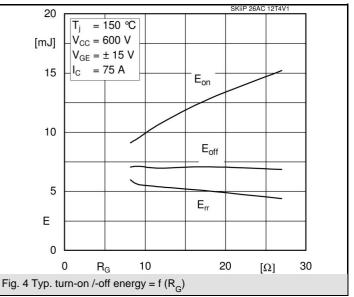


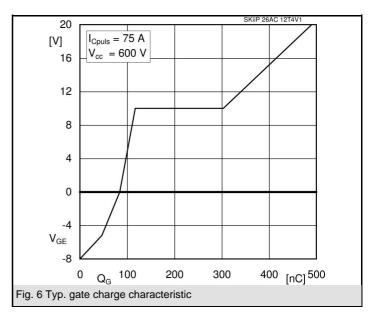


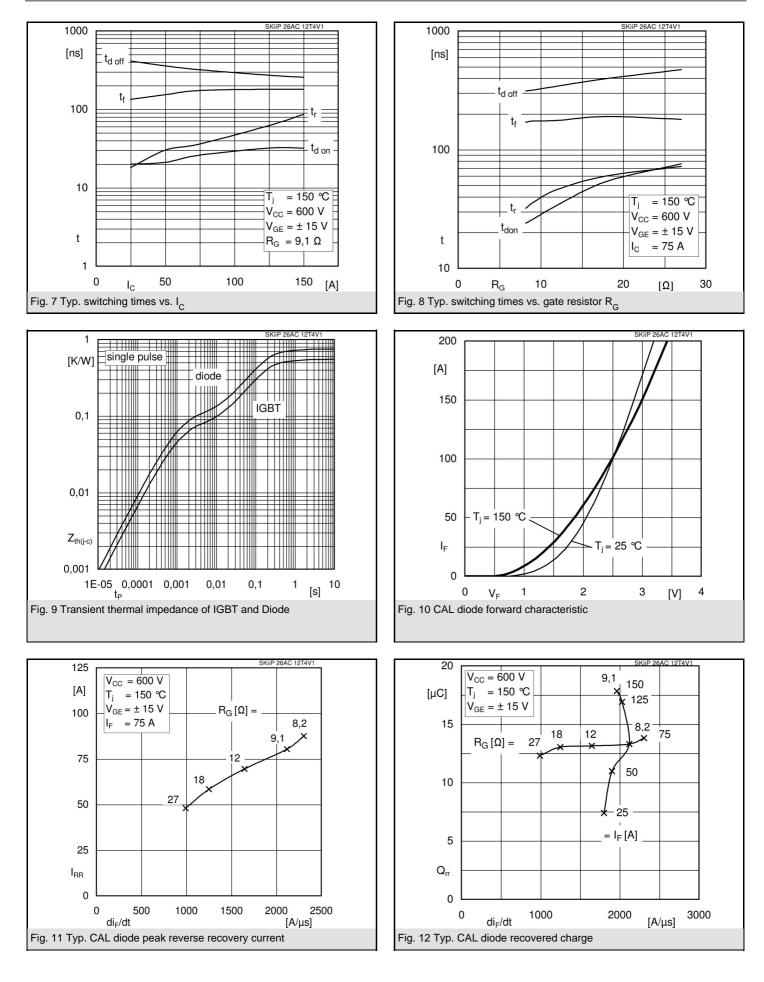












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